

IN THE CLAIMS

The following claim set replaces all prior versions, and listings, of claims in the application:

Claims 1-32 cancelled.

33. (amended) A nitride semiconductor light emitting device comprising; a substrate, an active layer, a p-type contact layer and a three layer laminated structure sandwiched by said substrate and said active layer, said three layer laminated structure having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer, an n-type cladding layer of nitride semiconductor between said third nitride semiconductor layer and said active layer, wherein said second nitride semiconductor layer is an n-type single layer having a thickness within a range of from 0.1 to 20 μ m,

wherein an impurity concentration of said first nitride semiconductor layer is set within $1\times10^{17}/\text{cm}^3$ and an impurity concentration of said third nitride semiconductor layer is set within $1\times10^{17}/\text{cm}^3$, and

wherein said second nitride semiconductor layer is a thick layer of which thickness is set $1\mu\text{m}$ or more and said third nitride semiconductor layer is a thin layer.

34. (amended) A nitride semiconductor light emitting device comprising; a substrate, an active layer, a p-type contact layer and a three layer laminated structure sandwiched by said substrate and said active layer, said three layer laminated structure having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer, an n-type cladding layer of nitride semiconductor between said third nitride semiconductor layer and said active layer, wherein said second nitride semiconductor layer is an n-type single layer having a thickness within a range of from 0.1 to 20 μ m,

wherein an impurity concentration of said first nitride semiconductor layer is set within $1\times 10^{17}/\text{cm}^3$ and an impurity concentration of said third nitride semiconductor layer is set within $1\times 10^{17}/\text{cm}^3$,

wherein and said second nitride semiconductor layer is a thick layer of which thickness is set 1 μ m or more and of which impurity concentration is set higher than that of said first and third nitride semiconductor layers,

wherein said third nitride semiconductor layer is a thin layer of which thickness is set not exceeding 0.5 μ m.

Claims 35-40 cancelled.

41.(amended)The nitride semiconductor light emitting device as in claim 31,32,
33, or 34 ~~or~~ 35, wherein said third nitride semiconductor layer is made of InGaN.

42. (canceled)

43. (amended) The nitride semiconductor light emitting device as in claim 31,32,
33, or 34 ~~or~~ 35, wherein said first to third nitride semiconductor layers have a same
composition.

44. (new) The nitride semiconductor light emitting device according to claim 43,
wherein said first to third nitride semiconductor layers are made of GaN.

Claim 45 cancelled.

46. (amended) The nitride semiconductor light emitting device as in claim 31,32,
33 or 34 ~~or~~ 35, wherein said second nitride semiconductor layer is a super lattice layer
made by laminating the low doped nitride semiconductor layers of n-type impurity and
the high doped nitride semiconductor layers of n-type impurity.

47. (new) The nitride semiconductor light emitting device according to claim 46,
wherein said second nitride semiconductor layer is a super lattice layer of combination of
nitride layers selected from the group consisting of GaN/GaN, InGaN/GaN, AlGaN/GaN
and InGaN/AlGaN.--

48. (added) A nitride semiconductor light emitting device comprising; a
substrate, an active layer, a p-type contact layer and a three layer laminated structure
sandwiched by said substrate and said active layer, said three layer laminated structure

having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer, a nitride semiconductor layer having Al between said third semiconductor layer and said active layer,

wherein said second nitride semiconductor layer is an n-type single layer having a thickness within a range of from 0.1 to 20 μ m,

wherein an impurity concentration of said first nitride semiconductor layer is set within $1\times10^{17}/\text{cm}^3$ and an impurity concentration of said third nitride semiconductor layer is set within $1\times10^{17}/\text{cm}^3$, and

wherein said second nitride semiconductor layer is a thick layer of which thickness is set 1 μ m or more and said third nitride semiconductor layer is a thin layer.

49. (added) A nitride semiconductor light emitting device comprising; a substrate, an active layer, a p-type contact layer and a three layer laminated structure sandwiched by said substrate and said active layer, said three layer laminated structure having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride

semiconductor layer and said active layer, a nitride semiconductor layer having Al between said third semiconductor layer and said active layer,
wherein said second nitride semiconductor layer is an n-type single layer having a thickness within a range of from 0.1 to 20 μ m,

wherein an impurity concentration of said first nitride semiconductor layer is set within $1\times 10^{17}/\text{cm}^3$ and an impurity concentration of said third nitride semiconductor layer is set within $1\times 10^{17}/\text{cm}^3$,

wherein said second nitride semiconductor layer is a thick layer of which thickness is set 1 μ m or more and of which impurity concentration is set higher than that of said first and third nitride semiconductor layers, and

wherein said third nitride semiconductor layer is a thin layer of which thickness is set not exceeding 0.5 μ m.

50.(added) The nitride semiconductor light emitting device as in claim 48 or 49, wherein said third nitride semiconductor layer is made of InGaN.

51. (added) The nitride semiconductor light emitting device as in claim 48 or 49, wherein said first to third nitride semiconductor layers have the same composition.

52. (added) The nitride semiconductor light emitting device according to claim 51, wherein said first to third nitride semiconductor layers are made of GaN.

53. (added) The nitride semiconductor light emitting device as in claim 48 or 49, wherein said second nitride semiconductor layer is a super lattice layer made by laminating the low doped nitride semiconductor layers of n-type impurity and the high doped nitride semiconductor layers of n-type impurity.

54. (added) The nitride semiconductor light emitting device according to claim 53, wherein said second nitride semiconductor layer is a super lattice layer of combination of nitride layers selected from the group consisting of GaN/GaN, InGaN/GaN, AlGaN/GaN and InGaN/AlGaN.

55. (added) A nitride semiconductor light emitting device comprising; a substrate, an active layer, a p-type contact layer and a three layer laminated structure sandwiched by said substrate and said active layer, said three layer laminated structure having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer,

wherein said second nitride semiconductor layer is an n-type single layer having a thickness within a range of from 0.1 to 20 μ m,

wherein an impurity concentration of said first nitride semiconductor layer is set within $1\times10^{17}/\text{cm}^3$ and an impurity concentration of said third nitride semiconductor layer is set within $1\times10^{17}/\text{cm}^3$,

wherein said second nitride semiconductor layer is a thick layer of which thickness is set $1\mu\text{m}$ or more and said third nitride semiconductor layer is a thin layer, and,

wherein said second nitride semiconductor layer is in contact with said first nitride semiconductor layer and said third nitride semiconductor layer.

56. (added) A nitride semiconductor light emitting device comprising; a substrate, an active layer, a p-type contact layer and a three layer laminated structure sandwiched by said substrate and said active layer, said three layer laminated structure having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer,

wherein said second nitride semiconductor layer is an n-type single layer having a thickness within a range of from 0.1 to $20\mu\text{m}$,

wherein an impurity concentration of said first nitride semiconductor layer is set within $1\times10^{17}/\text{cm}^3$ and an impurity concentration of said third nitride semiconductor layer is set within $1\times10^{17}/\text{cm}^3$,

wherein and said second nitride semiconductor layer is a thick layer of which thickness is set 1 μ m or more and of which impurity concentration is set higher than that of said first and third nitride semiconductor layers,

wherein said third nitride semiconductor layer is a thin layer of which thickness is set not exceeding 0.5 μ m and

wherein said second nitride semiconductor layer is in contact with said first nitride semiconductor layer and said third nitride semiconductor layer.

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57. (added) The nitride semiconductor light emitting device as in claim 55 or 56, wherein said third nitride semiconductor layer is made of InGaN.

58. (added) The nitride semiconductor light emitting device as in claim 55 or 56, wherein said first to third nitride semiconductor layers have a same composition.

59. (added) The nitride semiconductor light emitting device according to claim 58, wherein said first to third nitride semiconductor layers are made of GaN.

60. (added) The nitride semiconductor light emitting device as in claim 55 or 56, wherein said second nitride semiconductor layer is a super lattice layer made by laminating the low doped nitride semiconductor layers of n-type impurity and the high doped nitride semiconductor layers of n-type impurity.

61. (added) The nitride semiconductor light emitting device according to claim
60, wherein said second nitride semiconductor layer is a super lattice layer of
C1 combination of nitride layers selected from the group consisting of GaN/GaN,
InGaN/GaN, AlGaN/GaN and InGaN/AlGaN.
